

TOSHIBA Diode Silicon Epitaxial Planar Type

1SS370

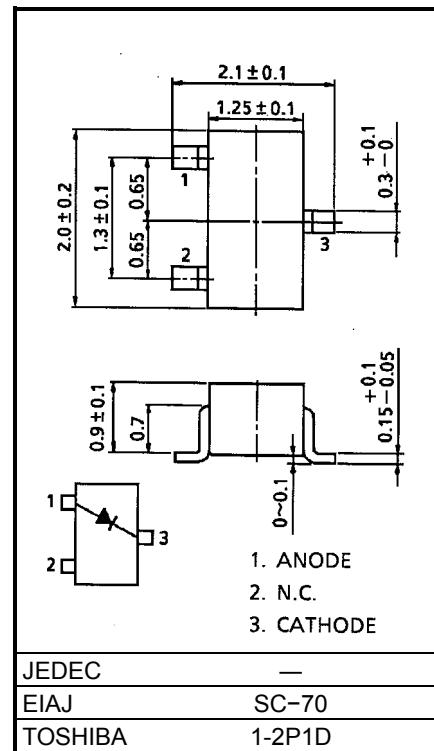
High Voltage, High Speed Switching Applications

Unit: mm

- Low forward voltage : $V_F(2) = 0.9V$ (typ.)
- Fast reverse recovery time: $t_{rr} = 60\text{ns}$ (typ.)
- Small total capacitance : $C_T = 1.5\text{pF}$ (typ.)
- Small package : SC-70

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	250	V
Reverse voltage	V_R	200	V
Maximum (peak) forward current	I_{FM}	300	mA
Average forward current	I_O	100	mA
Surge current (10ms)	I_{FSM}	2	A
Power dissipation	P	100	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C



Weight: 0.006g

Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Forward voltage	$V_F(1)$	—	$I_F = 10\text{mA}$	—	0.72	1.0	V
	$V_F(2)$	—	$I_F = 100\text{mA}$	—	0.90	1.2	
Reverse current	$I_R(1)$	—	$V_R = 50\text{V}$	—	—	0.1	μA
	$I_R(2)$	—	$V_R = 200\text{V}$	—	—	1.0	
Total capacitance	C_T	—	$V_R = 0, f = 1\text{MHz}$	—	1.5	3.0	pF
Reverse recovery time	t_{rr}	—	$I_F = 10\text{mA}$, Fig.1	—	10	60	ns